

Synchronous Rectifier Controller with Zero Voltage Switching for Wide Output Voltage Operating Range

1 General Description

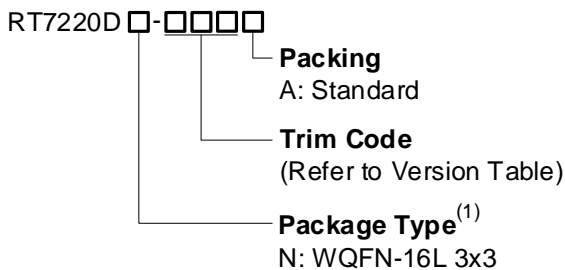
The RT7220D is a Synchronous Rectifier (SR) controller for Flyback converters operating in Continuous Conduction Mode (CCM), Discontinuous Conduction Mode (DCM) and Quasi-Resonant (QR) mode. The RT7220D will sense the drain voltage of MOSFET to determine SR gate on/off so as to minimize turn-off dead-time and enhance efficiency.

The RT7220D supports the wide output voltage range from 3V to 21V, and a HV LDO is especially built-in for the MOSFET gate driver at low output voltage. When it works with the primary-side controller RT7757, the Zero-Voltage-Switching (ZVS) control can be enabled to optimize the efficiency at high line.

Furthermore, the RT7220D provides a green mode operation in light load condition, which reduces operation current to be under 250μA.

The recommended junction temperature range is -40°C to 125°C, and the ambient temperature range is -40°C to 105°C.

2 Ordering Information



Note 1.

Richtek products are Richtek Green Policy compliant and marked with ⁽¹⁾ indicates compatible with the current requirements of IPC/JEDEC J-STD-020.

3 Features

- Suitable for Flyback Converter in CCM, DCM, and Quasi-Resonant (QR) Mode
- Suitable for 3V to 21V V_{OUT} Range
- ZVS Function to Optimize Efficiency (Work with the Primary-Side Controller RT7757)
- <1.65mA Operating Current in ZVS Mode
- <250μA Operating Current in Green Mode
- Built-In HV LDO to Supply SR Driver when V_{out} is Lower than 5V
- Automatic Dead-Time Tracking Control to Optimize Efficiency
- Protection
 - SR Gate Driver with 6V Clamp
 - SR Gate Initial Pull-Low before Start-Up
 - SR Minimum Off-Time
 - Fast Turn-Off (<50ns) Gate Driver

4 Applications

- USB PD Power Converters
- Fast-Charger Power Adapters
- General Purpose High-Efficiency and/or Compact-Size Flyback Power Converters

6.2 Simplified Circuit for High-Side Application

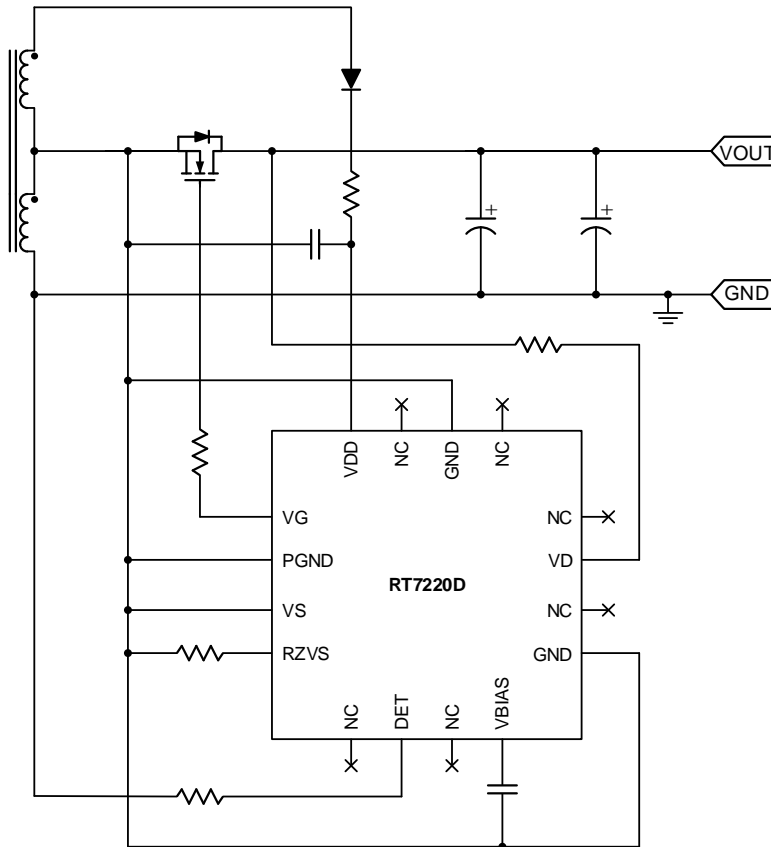


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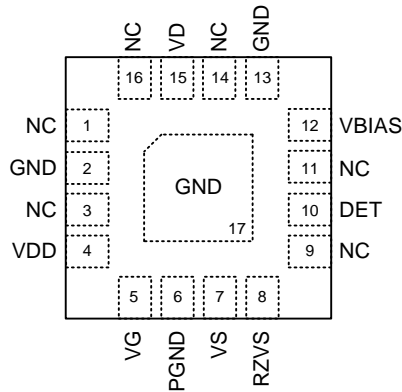
7 RT7220D Version Table

Version	RT7220DN-HQA (RT7220DHQGQW)	RT7220DN-LPA (RT7220DLPGQW)	RT7220DN-LMA
High/Low-Side Application	High-Side	Low-Side	Low-Side
VD Voltage Supported	180V	180V	180V
Output Voltage Supported	3V to 21V	3V to 21V	3V to 21V
Maximum Operation Frequency	160kHz	160kHz	160kHz
HV LDO	180V/65mA	180V/65mA	180V/65mA
ZVS Function	Enable	Enable	Enable
VOUT Range of Maximum Power Supported	18V to 21V	9V to 21V	18V to 21V
Frequency Jitter Range of ZVS Mode	±12%	±12%	±12%
Internal Rzvs (When the RZVS pin is short-circuited)	360kΩ	360kΩ	480kΩ
DET Pin Connection	300kΩ to System GND	Short to IC GND	Short to IC GND
Cooperated Primary-Side Controller (Note 2)	RT7757D-GEQA (RT7757GEQ)	RT7757D-GEPA (RT7757GEP)	RT7757D-AEMA

Note 2. The last two characters in the part numbers of both the RT7220D and the RT7757 must be the same. Otherwise, the ZVS function will not operate normally. (For example, RT7757D-AE"MA" ↔ RT7220DN-L"MA").

8 Pin Configuration

(TOP VIEW)

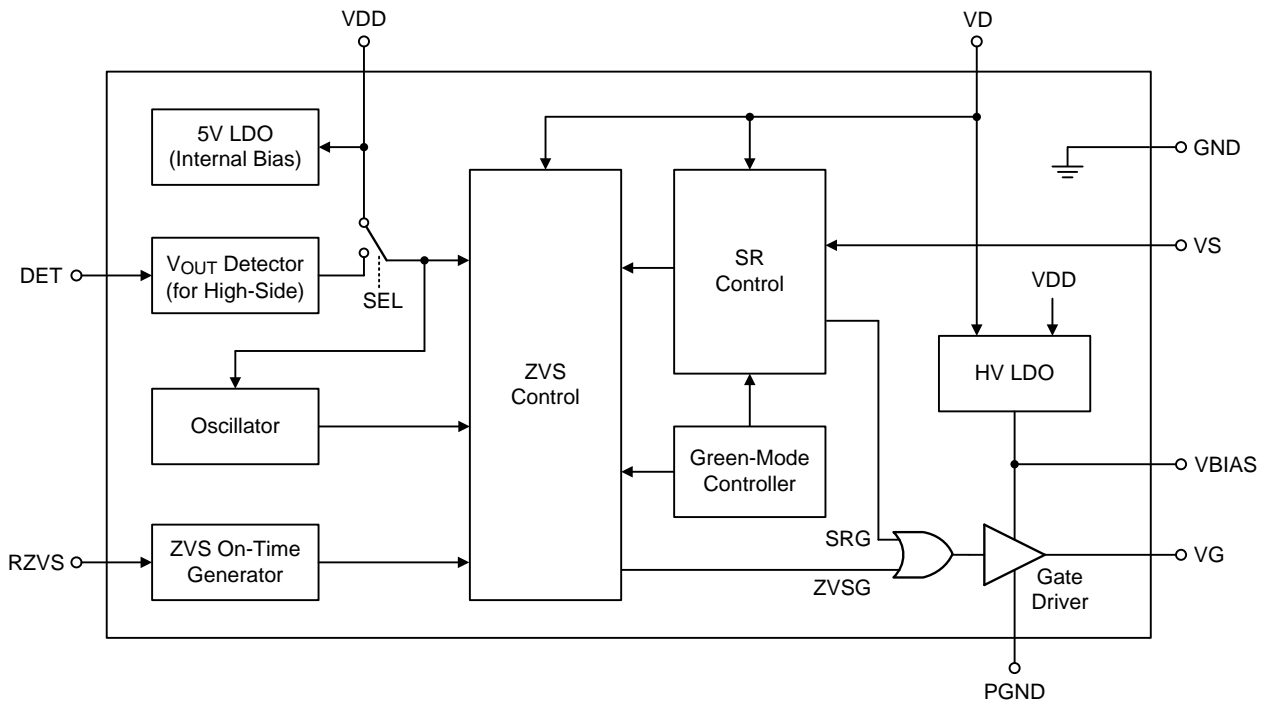


WQFN-16L 3x3

9 Functional Pin Description

Pin No.	Pin Name	Pin Function
1, 3, 9, 11, 14, 16	NC	No internal connection.
2, 13, 17 (Exposed Pad)	GND	Ground. The exposed pad must be connected to GND and well soldered to a large PCB copper area for maximum power dissipation.
4	VDD	Supply voltage.
5	VG	Gate driver output for the SR MOSFET.
6	PGND	Ground of gate driver.
7	VS	Source voltage sensing node for the SR MOSFET.
8	RZVS	ZVS on-time setting.
10	DET	Output voltage detection for high-side SR MOSFET.
12	VBIAS	Regulated DC bias.
15	VD	Drain voltage sense node for the SR MOSFET.

10 Functional Block Diagram



11 Absolute Maximum Ratings

(Note 3)

- VD to GND ----- -1V (pulse width 500ns) to 180V
- VDD to GND ----- -0.3V to 40V
- VBIAS to GND ----- -0.3V to 6.5V
- VG to GND ----- -0.3V to VBIAS + 0.3V
- RZVS to GND ----- -0.3V to 6.5V
- DET to GND ----- -1V to 6.5V
- Power Dissipation, PD @ TA = 25°C
 - WQFN-16L 3x3 ----- 2.35W
- Package Thermal Resistance (Note 4)
 - WQFN-16L 3x3, θ_{JA} ----- 42.5°C/W
 - WQFN-16L 3x3, θ_{JC} ----- 7.5°C/W
- Junction Temperature ----- 150°C
- Lead Temperature (Soldering, 10sec.) ----- 260°C
- Storage Temperature Range ----- -65°C to 150°C
- ESD Susceptibility (Note 5)
 - HBM (Human Body Model) ----- 2kV

Note 3. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Note 4. θ_{JA} is measured under natural convection (still air) at TA = 25°C with the component mounted on a low effective-thermal-conductivity two-layer test board on a JEDEC thermal measurement standard. θ_{JC} is measured at the bottom of the package.

Note 5. Devices are ESD sensitive. Handling precautions are recommended.

12 Recommended Operating Conditions

(Note 6)

- Supply Input Voltage, VD ----- -1V (pulse width 500ns) to 150V
- Supply Input Voltage, VDD ----- 3V to 36V
- Junction Temperature Range ----- -40°C to 125°C
- Ambient Temperature Range ----- -40°C to 105°C

Note 6. The device is not guaranteed to function outside its operating conditions.

13 Electrical Characteristics

(T_A = 25°C, unless otherwise specified.)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
VDD Section						
VDD Turn-On Threshold Voltage	V _{VDD_ON}		3.1	3.25	3.4	V
VDD Turn-Off Threshold Voltage	V _{VDD_OFF}		2.6	2.75	2.9	V
Hysteresis Voltage for VDD Turn-On/VDD Turn-Off Threshold	V _{VDD_HYST}		0.4	0.5	0.6	V
VDD Start-Up Current	I _{DD_START}	V _{DD} = V _{VDD_ON} - 1V	--	--	150	μA
VDD Operating Current	I _{DD_OP}	V _{DD} = 5V, the VG pin is open, only enable SR function.	--	1.2	1.5	mA
VDD Operating Current	I _{DD_OP_ZVS}	V _{DD} = 5V, the VG pin is open, enable SR and ZVS function.	--	1.35	1.65	mA
VDD Green-Mode Current	I _{DD_GREEN}	In green mode. V _{DD} = 5V	--	200	250	μA
VBIAS Section						
VBIAS Output Voltage	V _{BIAS}	I _{LOAD} = 15mA, V _{DD} > 6V	5.5	6	6.5	V
		I _{LOAD} = 5mA, 4.7V < V _{DD} < 6V	V _{DD} - 0.15	--	V _{DD}	
		I _{LOAD} = 5mA, V _{DD} < 4.7V, 9V < V _D < 150V, V _D duty > 20% at 200kHz. The power path for the SR driver is from the V _D and cycle-by-cycle to detect V _{DD} to change power source.	4.5	4.7	4.9	
VBIAS Load Regulation		1mA < I _{VBIAS} < 15mA (Continuance) (Note 7)	--	--	200	mV
VBIAS Output Short Circuit Current	I _{VBIAS_SC}		50	65	80	mA
SR Driver Section						
Output High Voltage	V _{OH_VG}	I _{LOAD} = 20mA	V _{BIAS} - 0.3	--	V _{BIAS}	V
Output Low Voltage	V _{OL_VG}		--	--	0.5	V
Rise Time	t _{R_VG}	C _L = 4nF, V _G is from 1V to 4V	--	50	100	ns
Turn-On Propagation Time	t _{P_ON}	From trigger V _D falling edge to V _G = 0.1V.	--	--	80	ns
Fall Time	t _{F_VG}	C _L = 4nF, from 80% x V _{OH_VG} to 1V	--	--	15	ns
Turn-Off Propagation Time	t _{P_OFF}		--	--	30	ns
Initial Output Low Clamping Voltage before Start-up	V _{OL_VG_INI}	C _{GD} = 330pF, C _{GS} = 27pF, V _D is from 0V to 40V, t _R = 50ns, pulse width = 1μs. (Note 7)	--	--	1.5	V
Internal Pull-Low Resistor	R _{GS_LOW}		70	100	130	kΩ

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
VD Section						
V _{DS} Scaling Ratio I	K _{VDS_I}	For SR function (Note 7)	--	2	--	%
V _{DS} Scaling Ratio II	K _{VDS_II}	For ZVS function (Note 7)	--	15	--	
VD Sample and Hold Error	E _{SH_VD}	$(V_{VD_HIGH} - V_{VD_SH} /V_{VD_SH}) \times 100$	--	--	±5	%
Threshold of VD Sample and Hold	V _{VD_SH}	$V_{TH_SH} = K_{VD_SH} \times V_{VD_HIGH}[n-1]$	--	0.7	--	--
Mask Time	t _{MASK}	$V_{VD} > V_{TH_SH}$ (Note 7)	100	120	140	ns
Initial VD Blanking Time	t _{BLANK_VD_INI}	VD blanking time is counted after t _{MASK}	0.2	0.3	0.4	μs
V _{IN} Low VD Blanking Time	t _{BLANK_VD_VINL}	VD blanking time is counted after t _{MASK}	0.9	1.05	1.2	μs
Low Level Threshold for Input Voltage	K _{VIN_LOW}	When $V_{DS} < K_{VIN_LOW} \times V_{DD}$, VD blanking time will be changed to V _{IN} low blanking time and minimum off-time.	2	2.2	2.4	--
Low Level Threshold for VD Falling Edge Detection	V _{LOW_FALLING}		-0.4	-0.3	-0.2	V
Dead Time Comparison High Threshold	V _{TH_DT}		0.4	0.5	0.6	V
VG Fast Turn-Off Initial Threshold	V _{TH_VGOFF_INI}		-13	-10	-7	mV
Maximum VG Fast Turn-Off Limit for Tracking Up/Down	V _{VGOFF_MAX}	With 8-bit tracking control	17	20	23	mV
VG Fast Turn-Off Step Limit for Tracking Up/Down	ΔV _{VGOFF}	$V_{TH_VGOFF}[n] = V_{TH_VGOFF}[n-1] \pm \Delta V_{VGOFF}$	0.062	0.078	0.094	mV
VD Falling Time Threshold for VG Trigger	t _{VD_FALLING}	VD falling edge is from V _{TH_SH} to V _{LOW_FALLING} . If VD falling time < t _{VD_FALLING} and disable VD falling edge debounce time, VG will be triggered immediately when VD < V _{LOW_FALLING} .	100	150	200	ns
VD Edge Threshold for Exit Green Mode Detection	V _{VD_EDGE}		-0.4	-0.3	-0.2	V
Debounce Time for Exit/Enter Green Mode Detection	t _{VD_EDGE}		4	5	6	ms
VD Cycle Number for Enter Green Mode	N _{ENGR}	The number of VG pulses in t _{VD_EDGE} is less than N _{ENGR} .	--	16	--	--
VD Cycle Number for Exit Green Mode	N _{EXGR}	The number of VD pulses in t _{VD_EDGE} is greater than N _{EXGR} .	--	32	--	--
VD Cycle Number for Fast Exit Green Mode	N _{EXGR_F}	The number of continuous VG pulses is greater than N _{EXGR_F} .	--	8	--	--

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
SR Control Section							
VG Minimum On-Time	tMINON_VG	From VG rising edge to VG falling edge. (Note 7)	RT7220DN-HQA, RT7220DN-LPA	400	500	600	ns
			RT7220DN-LMA	800	1000	1200	
Disable VG Minimum On- Time Threshold	VMINON_DIS	When VD > VMINON_DIS during tMINON_VG, VG will be disabled immediately.	0.4	0.5	0.6	V	
Initial VG Minimum Off-Time	tMINOFF_VG_INI	From VG falling edge to the next VG rising edge.	0.2	0.3	0.4	μs	
VIN Low VG Minimum Off-Time	tMINOFF_VG_VINL	From VG falling edge to the next VG rising edge.	0.9	1.05	1.2	μs	
VD Undervoltage Protection Threshold	VVD_UVP	When VD < VVD_UVP, VG will be disabled. (Note 7)	--	--	VOUT + 3.5	V	
Automatic Tracking Section							
Auto-Tracking Dead Time	tDEAD_TRACK	From VG falling edge to VD = VTH_DT	180	200	220	ns	
Oscillator Section (Only for ZVS Function)							
Maximum Frequency	fOSC_MAX	VCTL > VFR_ET, Not including ZVS on-time.	110	120	130	kHz	
Minimum Frequency	fOSC_MIN	VCTL < VFR_EX	20	25	30	kHz	
Frequency Jittering Range	Δf		±9	±12	±15	%	
Frequency Jittering Period	tJIT	(Note 7)	--	512	--	cycle	
Frequency Variation Versus Temperature Deviation	fDT	TA = -30°C to 105°C (Note 7)	--	--	±6	%	
Internal RSET for Frequency Reduction Mode Control Voltage Modulation	RSET	(Note 7)	RT7220DN-HQA	--	380	--	kΩ
			RT7220DN-LPA	--	240	--	
			RT7220DN-LMA	--	340	--	
VOUT Scaling Ratio	KVO	(Note 7)	14.5	15	15.5	%	
Accuracy of Frequency Reduction Mode Control Voltage	ΔVCTL	$V_{CTL} = (10^{11} \times KVO \times L_m \times I_{peak}) / (3 \times NPS \times RSET)$	--	--	±7	%	
Boundary Voltage of Maximum Power	VFRMOD_MAX		RT7220DN-HQA, RT7220DN-LMA	2.6	2.7	2.8	V
			RT7220DN-LPA	1.25	1.35	1.45	

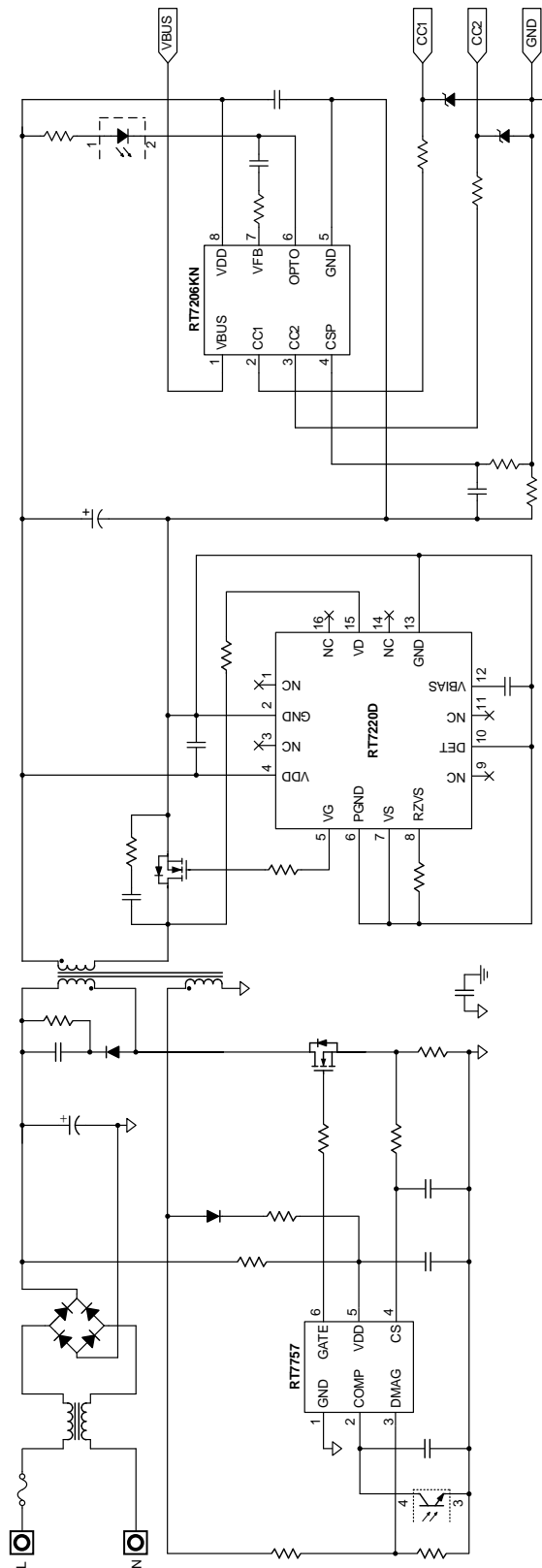
Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Boundary Voltage of Minimum Power	VFRMOD_MIN		RT7220DN-HQA, RT7220DN-LMA	0.8	0.9	1	V
			RT7220DN-LPA	0.5	0.6	0.7	
Entry Voltage of Frequency Reduction Mode	VFR_ET	$K_{VO} \times V_{OUT} > V_{FRMOD_MAX}$	RT7220DN-HQA, RT7220DN-LMA	1.55	1.6	1.65	V
		$K_{VO} \times V_{OUT} < V_{FRMOD_MIN}$		1.15	1.2	1.25	
		$K_{VO} \times V_{OUT} > V_{FRMOD_MAX}$	RT7220DN-LPA	1.4	1.45	1.5	
		$K_{VO} \times V_{OUT} < V_{FRMOD_MIN}$		1.15	1.2	1.25	
Exit Voltage of Frequency Reduction Mode	VFR_EX	$K_{VO} \times V_{OUT} > V_{FRMOD_MAX}$	RT7220DN-HQA, RT7220DN-LMA	1.2	1.25	1.3	V
		$K_{VO} \times V_{OUT} < V_{FRMOD_MIN}$		0.8	0.85	0.9	
		$K_{VO} \times V_{OUT} > V_{FRMOD_MAX}$	RT7220DN-LPA	1.05	1.1	1.15	
		$K_{VO} \times V_{OUT} < V_{FRMOD_MIN}$		0.8	0.85	0.9	
ZVS Section							
Maximum Count of PWM MOSFET Ringing Peak for ZVS Operation	NPEAK	Enable ZVS function when the number of VD valley $< N_{PEAK}$ (Note 7)	RT7220DN-HQA, RT7220DN-LPA	--	7	--	Peak
			RT7220DN-LMA	--	10	--	
ZVS Pulse Trigger Threshold	VTH_ZVS	If VD ringing $< V_{TH_ZVS}$, ZVS pulse will be triggered.		$0.95 \times V_{OUT}$	VOUT	$1.05 \times V_{OUT}$	V
ZVS Pulse Trigger Debounce Time	tD_PEAK	From $VD < V_{TH_ZVS}$ to ZVS Pulse rising edge.		100	200	300	ns
External RZVS Range for ZVS On-Time Setting	RZVS	The RZVS pin adds an external resistor, and a 1% resistor is suggested. (Note 7)		200	--	500	kΩ
Maximum ZVS On-Time	ton_ZVS_MAX	(Note 7)		3.5	4.4	5.3	μs
Minimum ZVS On-Time	ton_ZVS_MIN	ZVS pulse at first peak of primary-side MOSFET Vds	RT7220DN-HQA, RT7220DN-LPA	350	450	550	ns
			RT7220DN-LMA	700	900	1100	
		ZVS pulse at/after second peak of primary-side MOSFET Vds (Note 7)			350	450	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
ZVS On-Time Accuracy	t _{ON_ZVS}	R _{ZVS} = 480kΩ, V _D = 70V, V _{OUT} = 6.5V	2173	2557	2940	ns
		R _{ZVS} = 360kΩ, V _D = 70V, V _{OUT} = 6.5V	1588	1868	2148	
		R _{ZVS} = 240kΩ, V _D = 70V, V _{OUT} = 6.5V	901	1178	1455	
		R _{ZVS} = 480kΩ, V _D = 85V, V _{OUT} = 15V	957	1251	1545	
		R _{ZVS} = 360kΩ, V _D = 85V, V _{OUT} = 10V	1095	1432	1769	
V _{OUT} Threshold Voltage of Disable ZVS Operation	V _{TH_DISZVS}	If V _{OUT} < V _{TH_DISZVS} , ZVS function is disabled.	3.8	4.3	4.8	V
DET Section (Only for RT7220DN-HxA)						
External R _{DET}	R _{DET}	1% resistor is suggested. (Note 7)	--	300	--	kΩ
The DET Pin High-Level Clamping Voltage	V _{DET_CLAMP_H}		--	--	5.5	V
The DET Pin Low-Level Clamping Voltage	V _{DET_CLAMP_L}		-100	0	100	mV
Maximum DET Sourcing Current	I _{DET_MAX}		100	--	--	μA

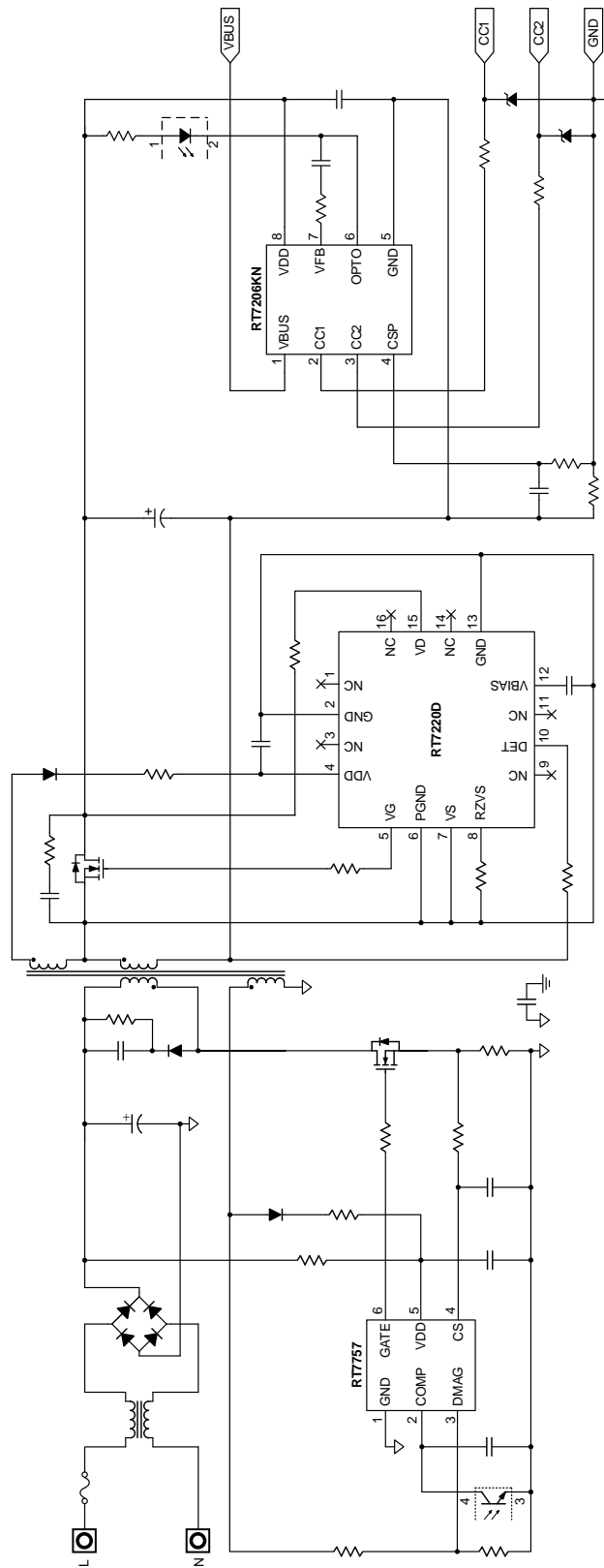
Note 7. Guaranteed by design.

14 Typical Application Circuit

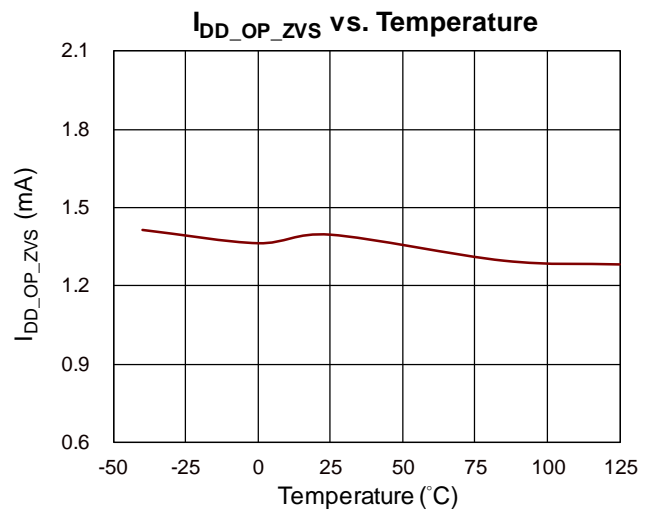
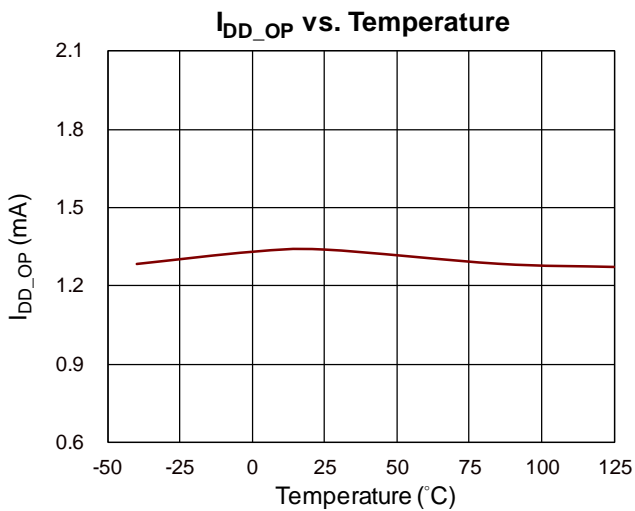
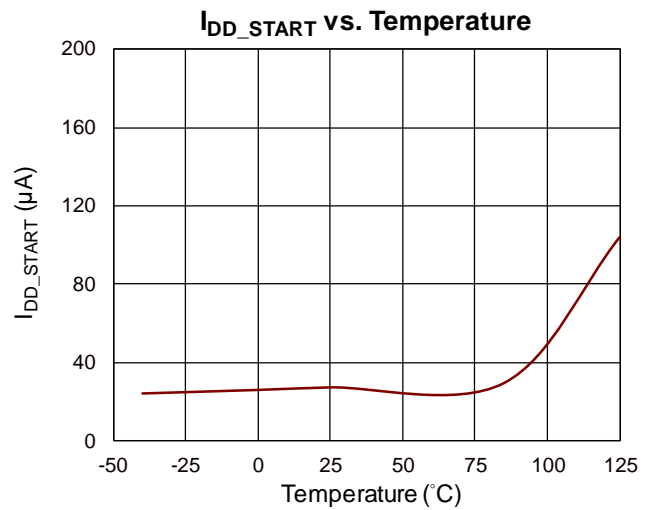
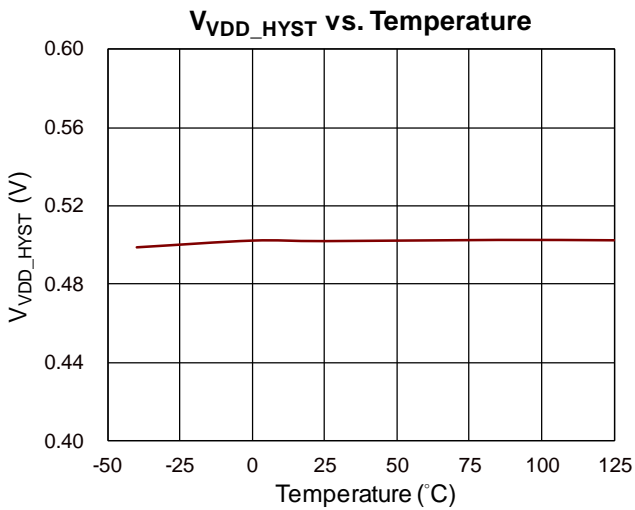
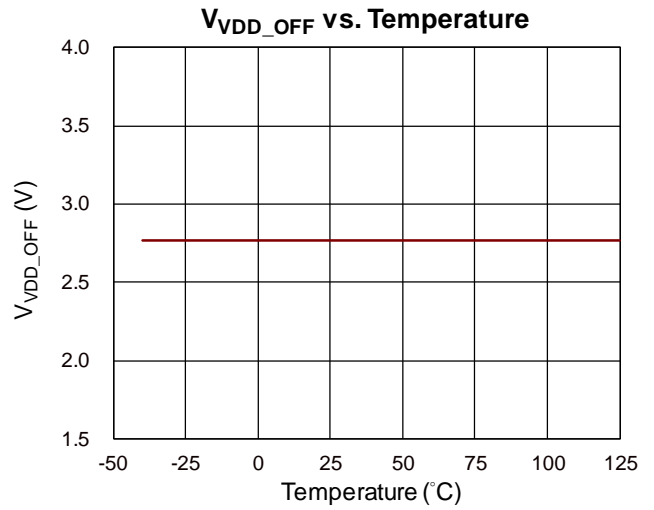
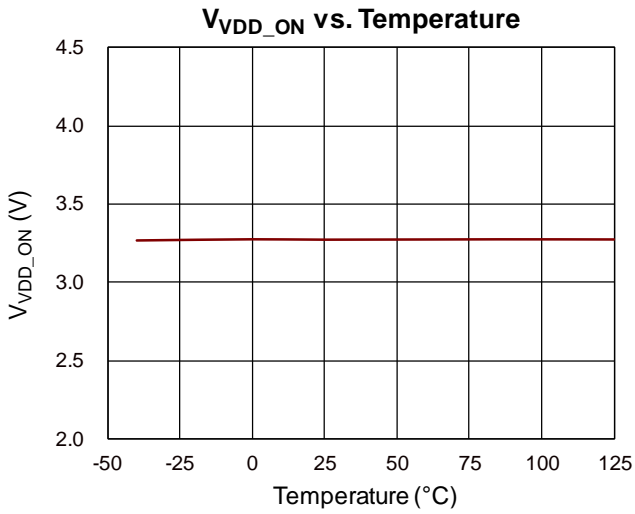
14.1 Typical Application Circuit for Low-Side Application

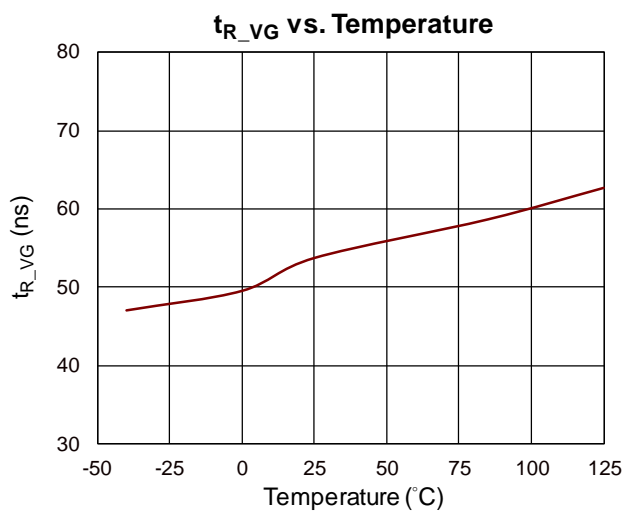
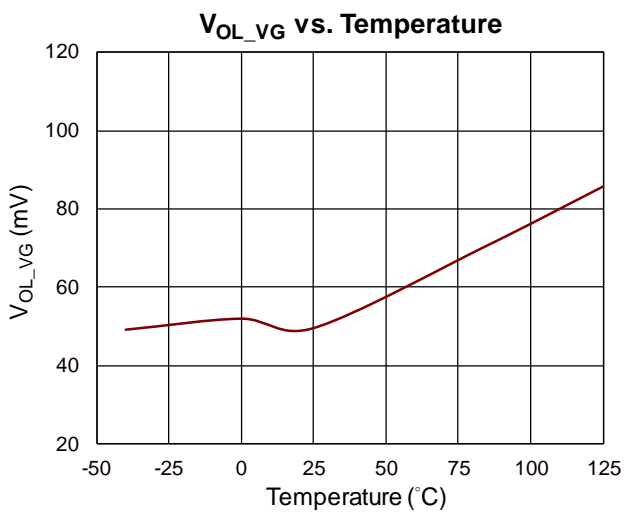
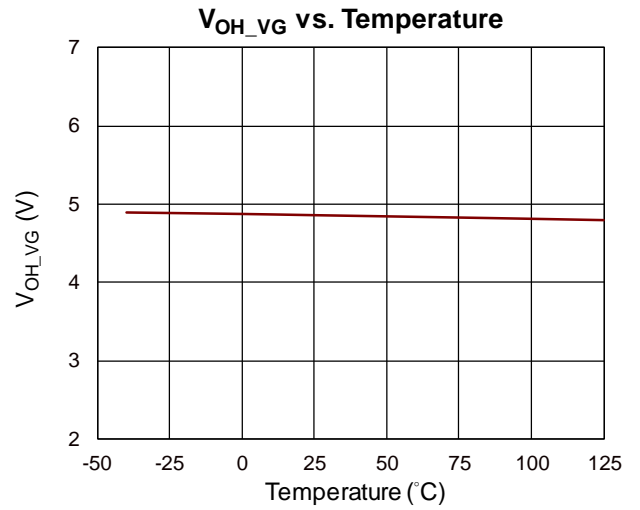
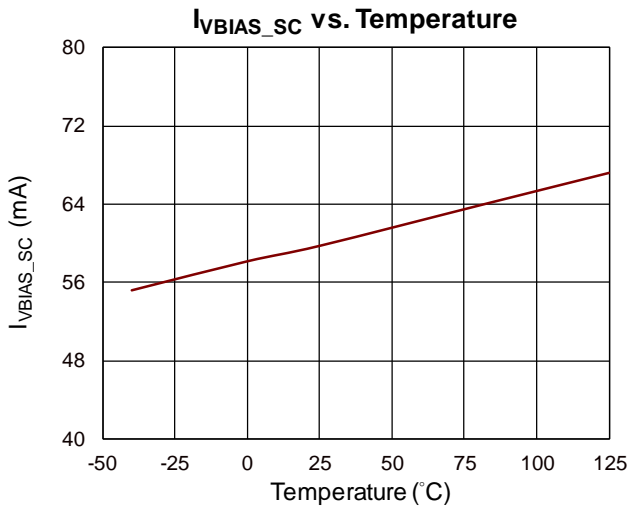
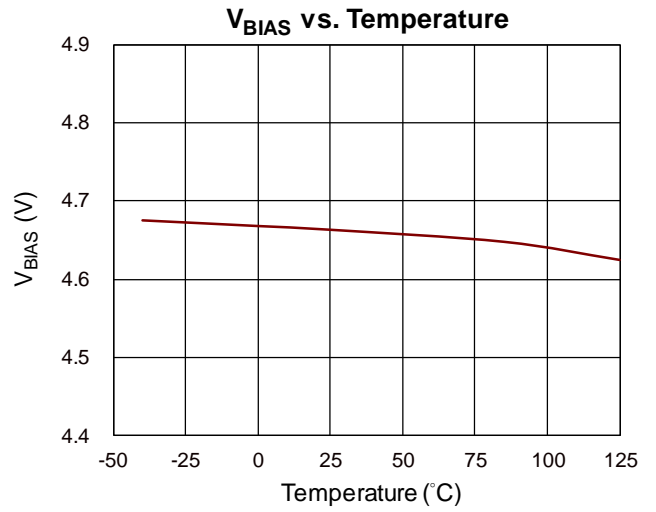
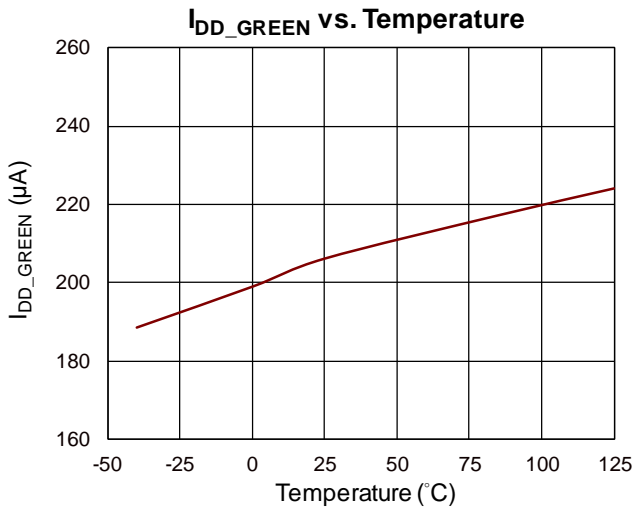


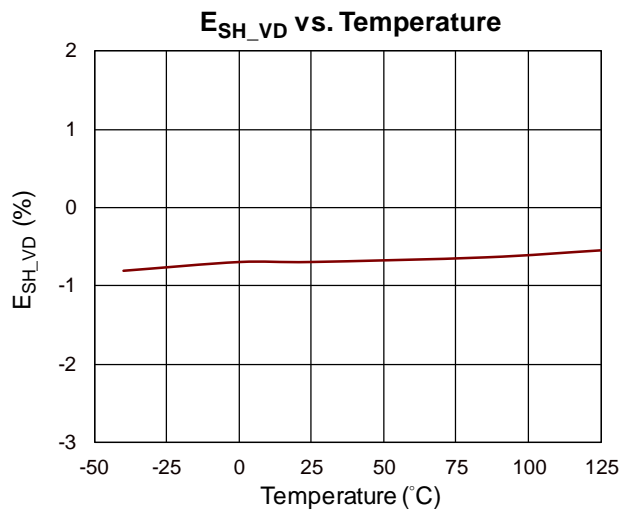
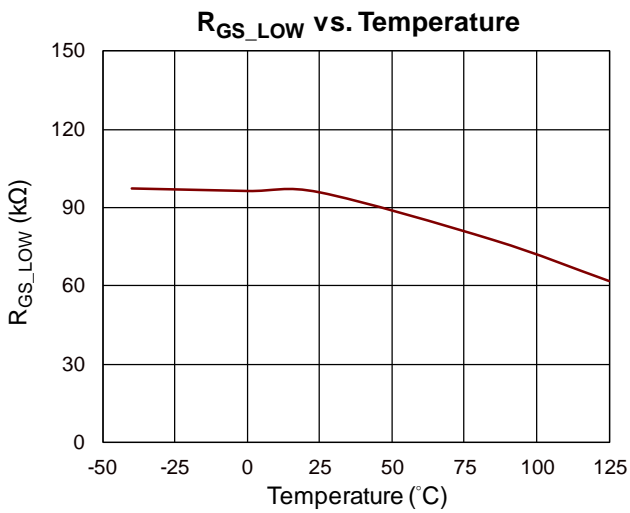
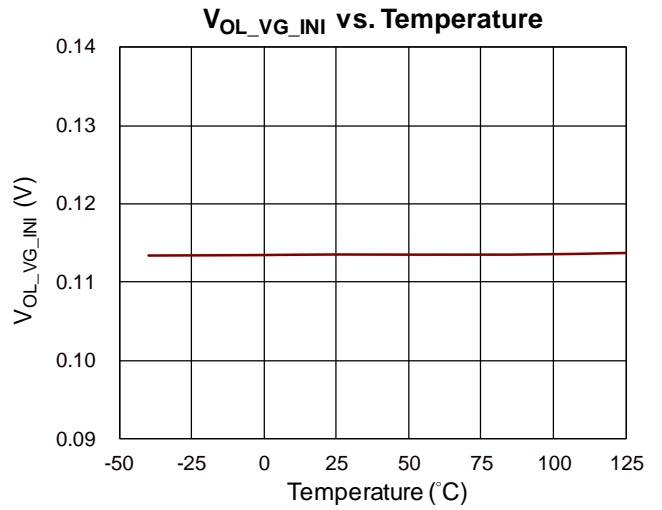
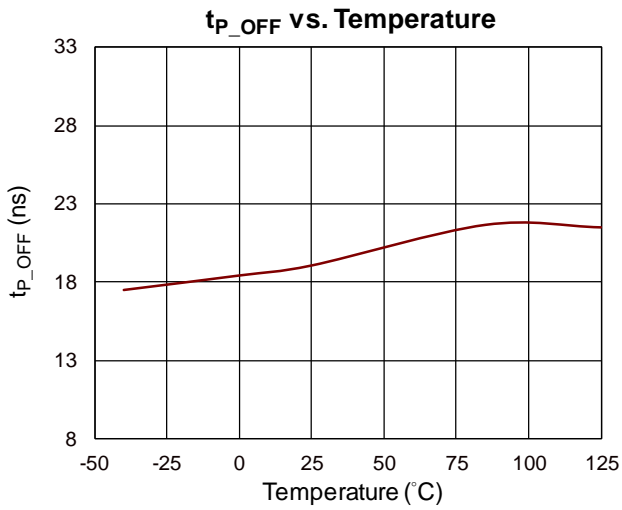
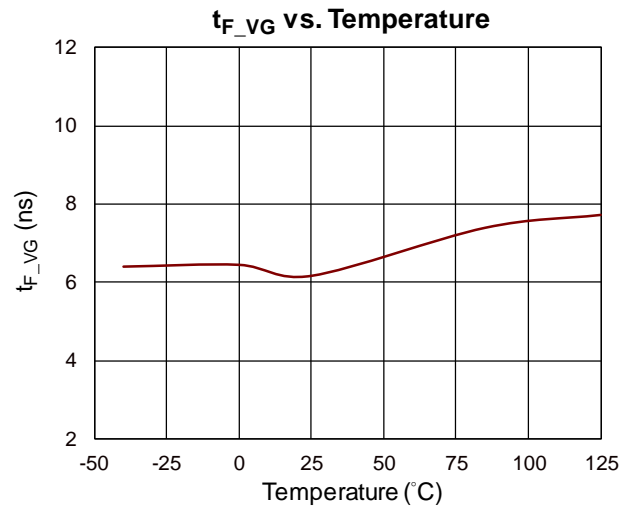
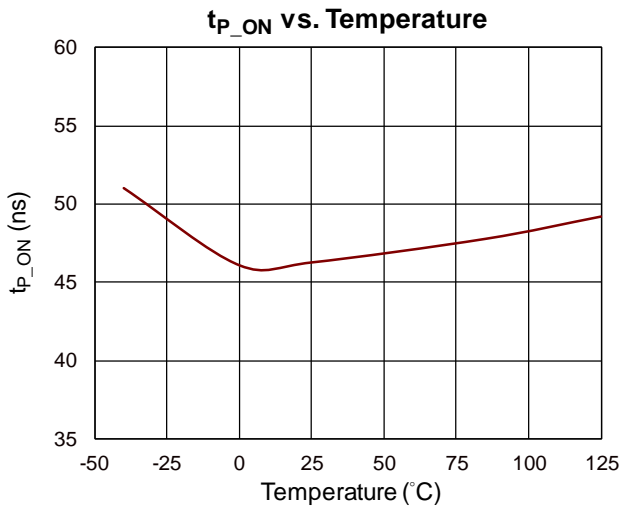
14.2 Typical Application Circuit for High-Side Application

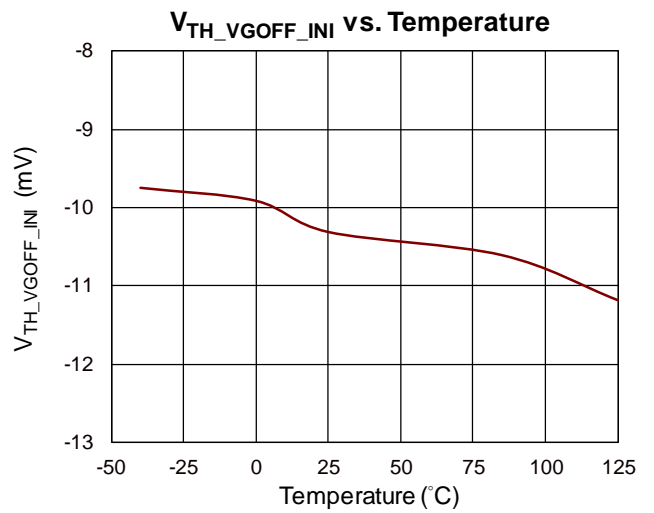
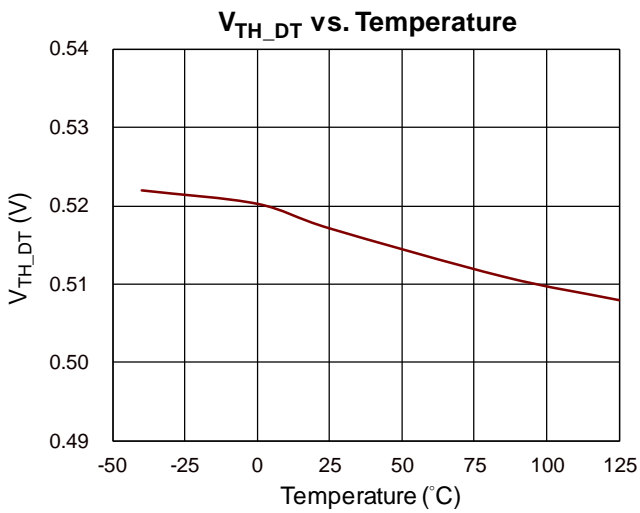
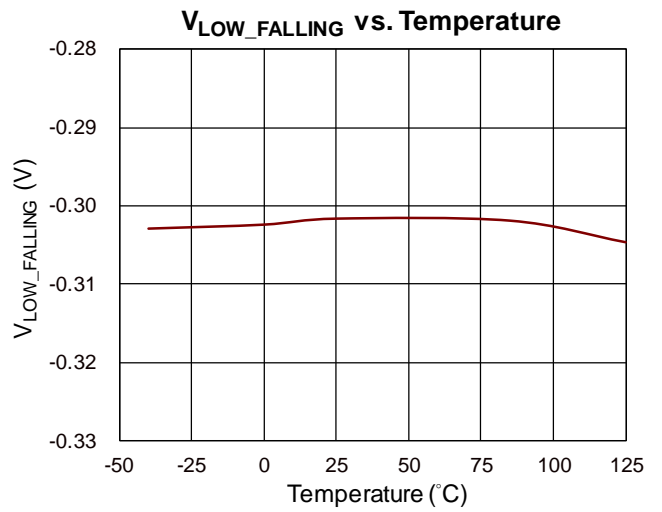
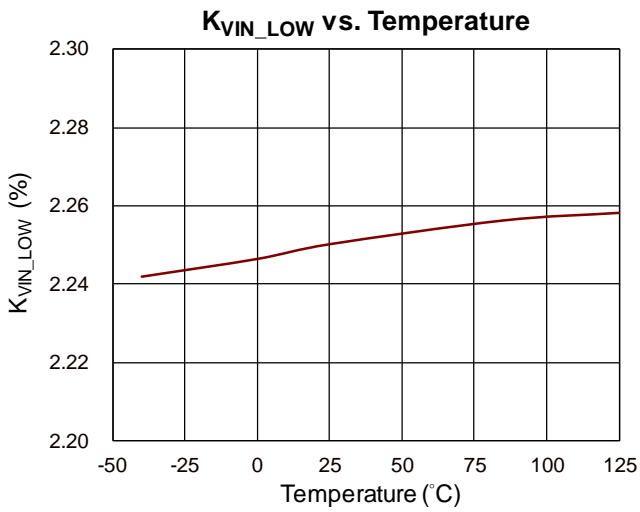
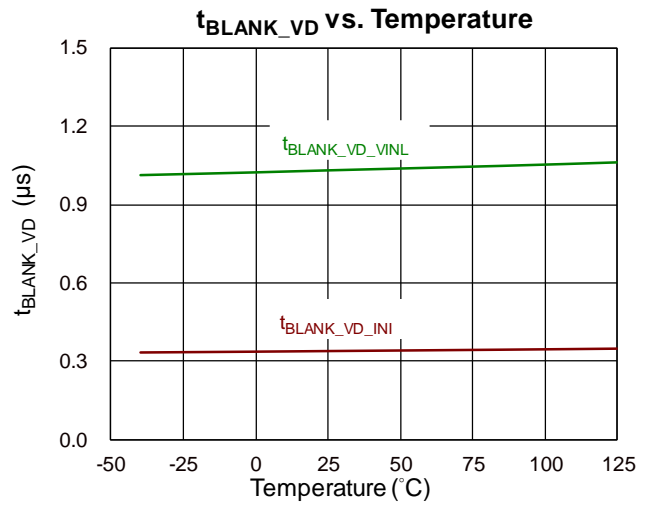
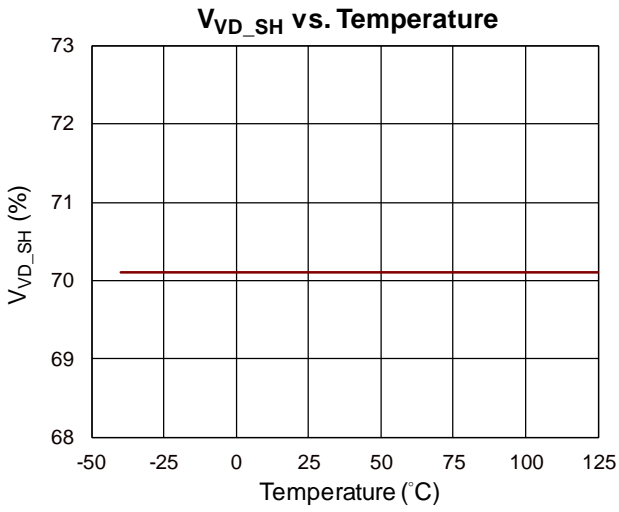


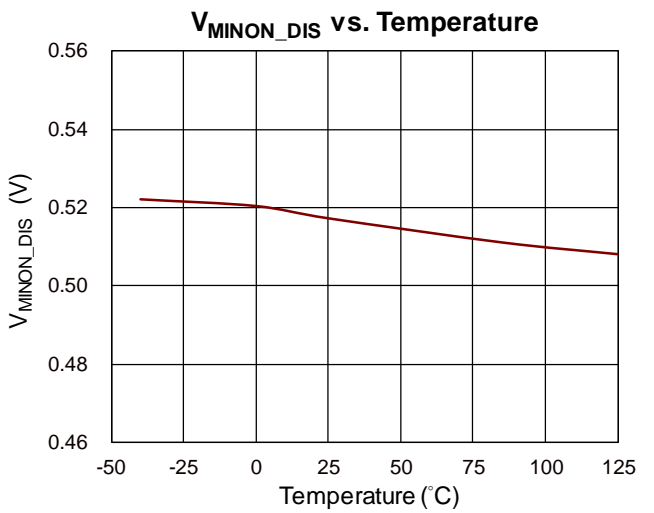
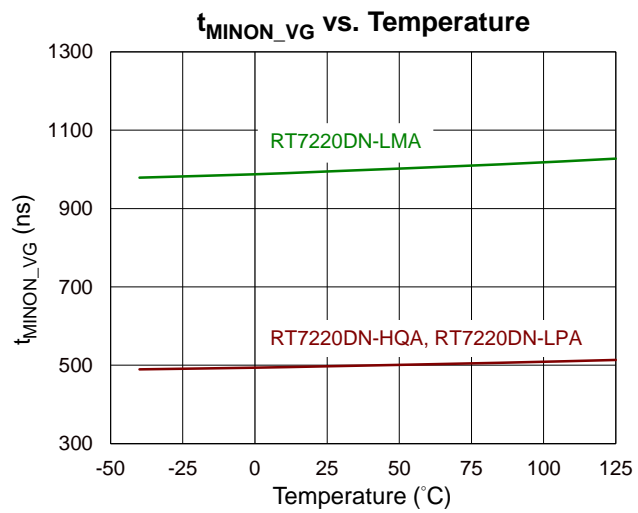
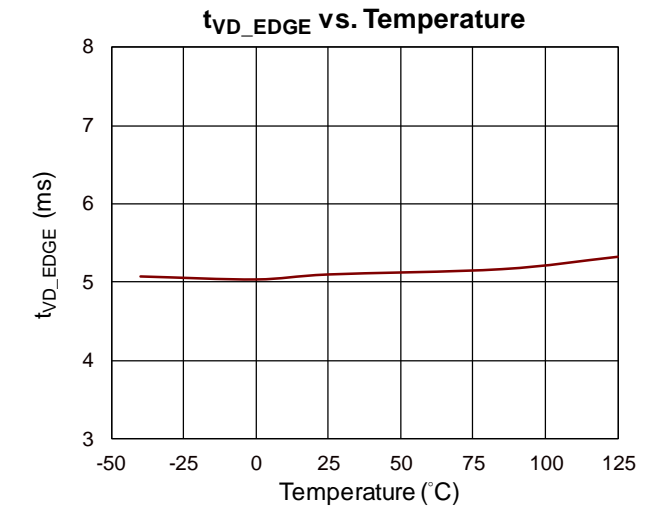
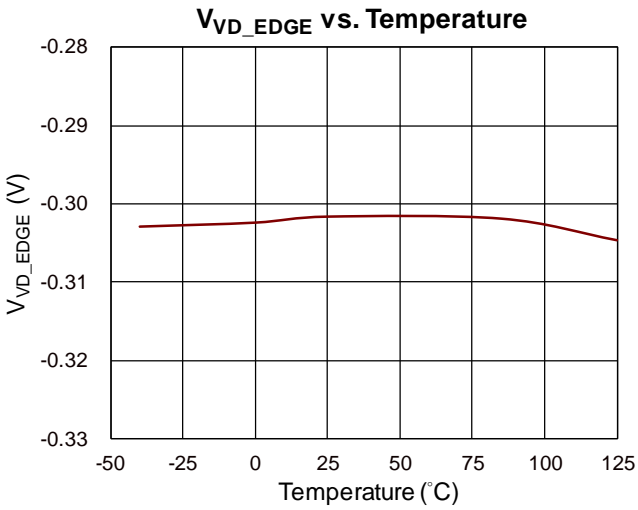
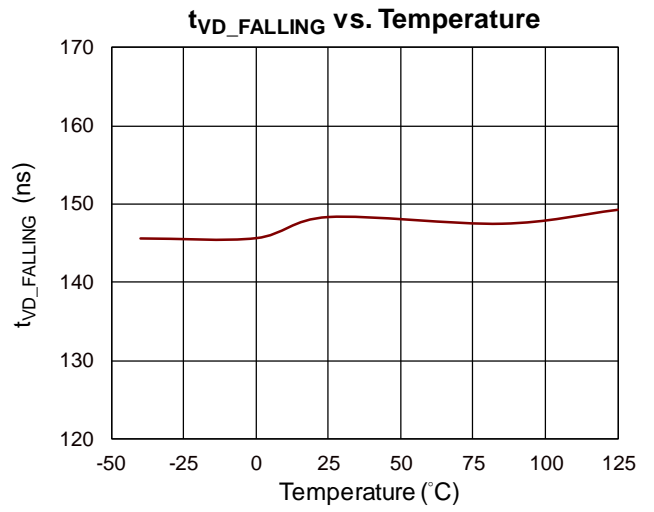
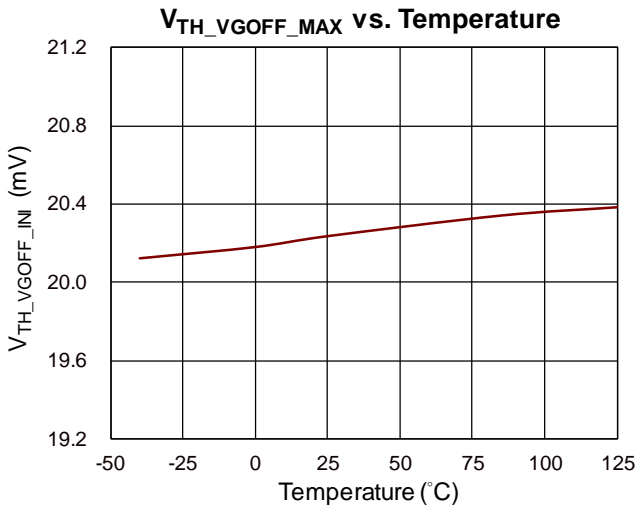
15 Typical Operating Characteristics

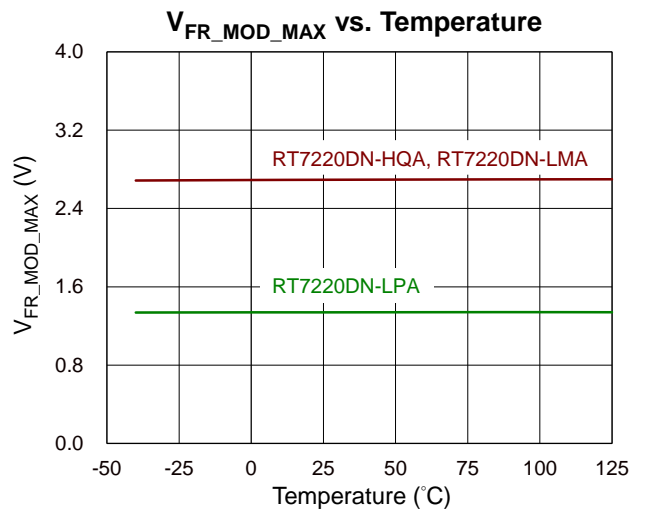
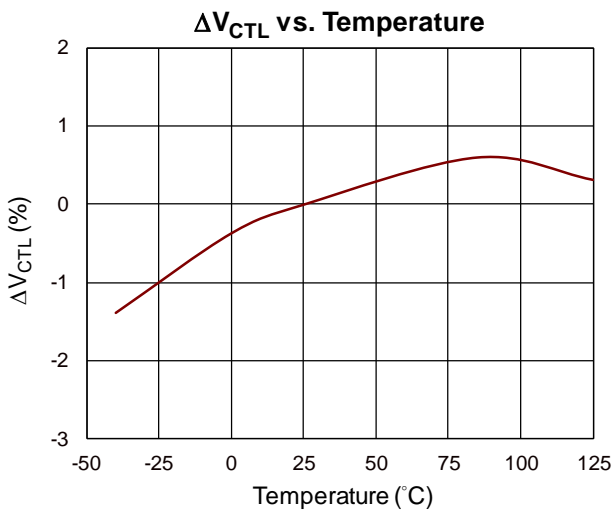
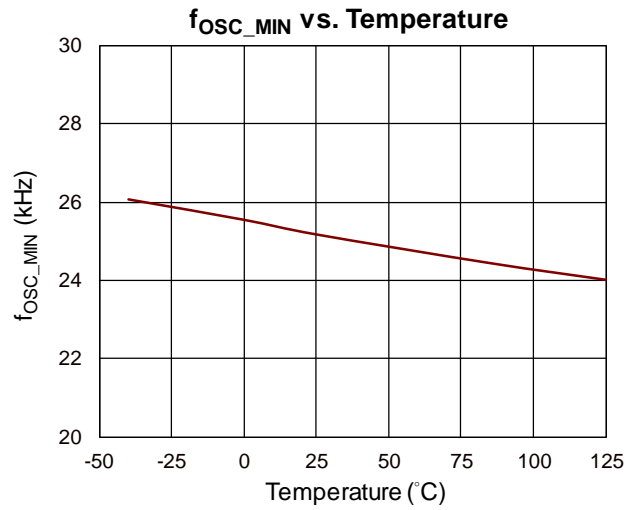
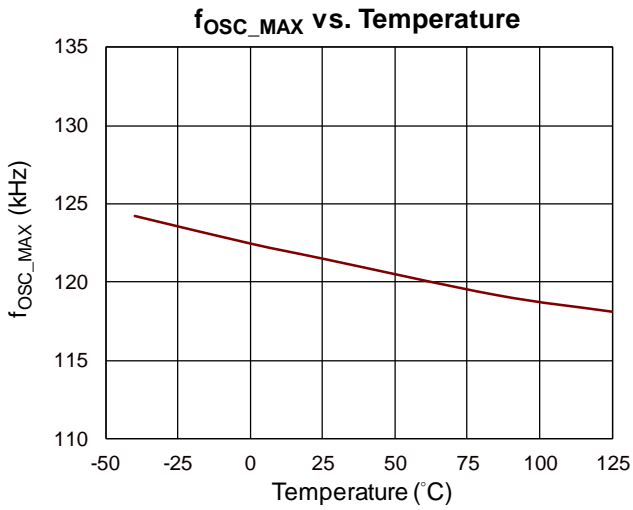
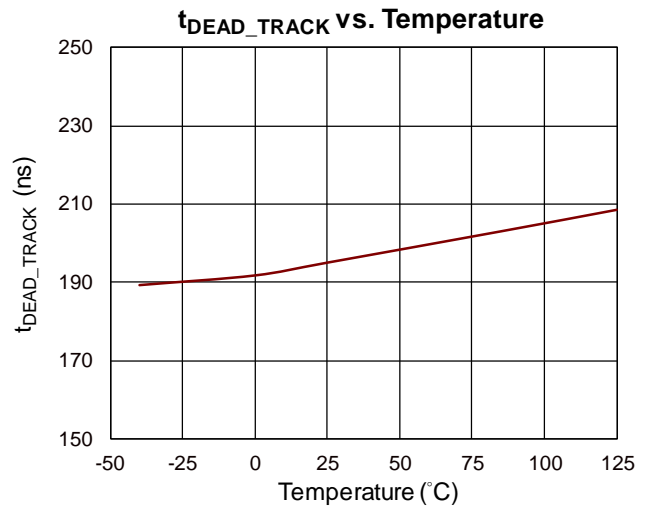
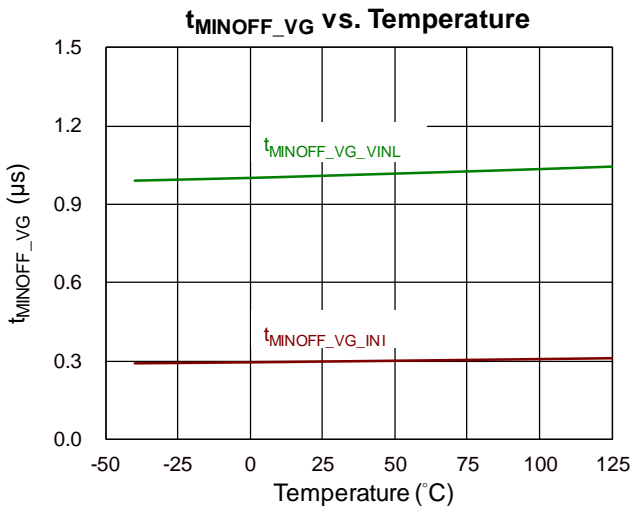




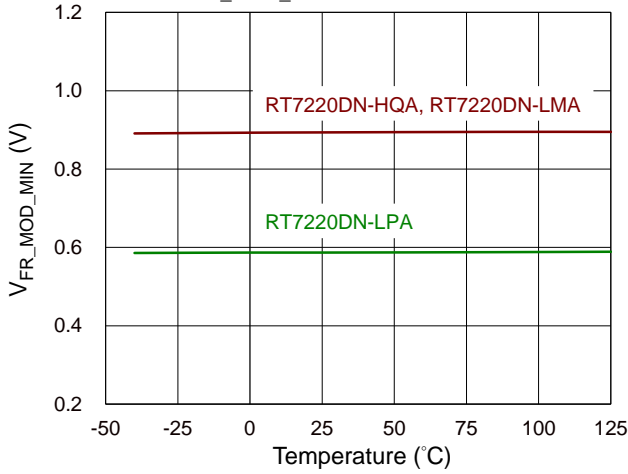




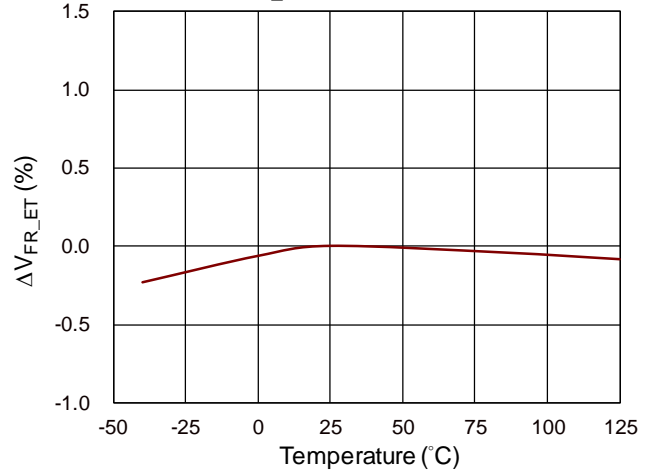




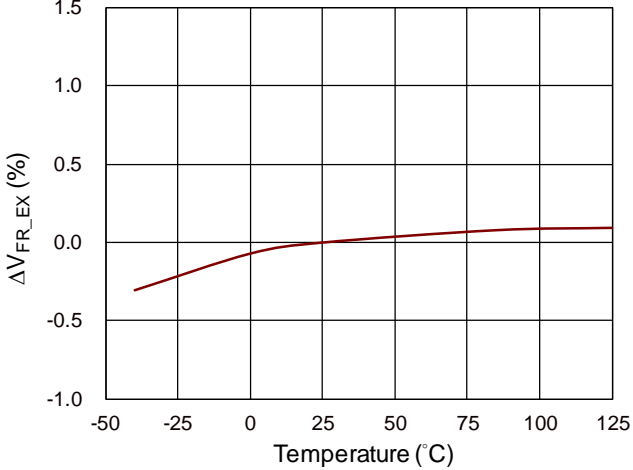
V_{FR_MOD_MIN} vs. Temperature



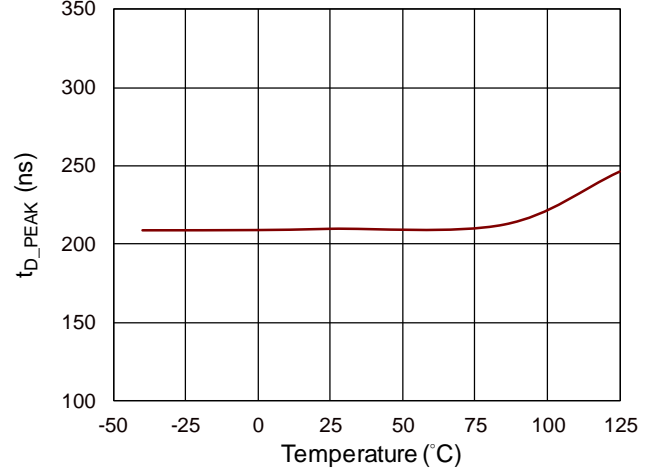
ΔV_{FR_ET} vs. Temperature



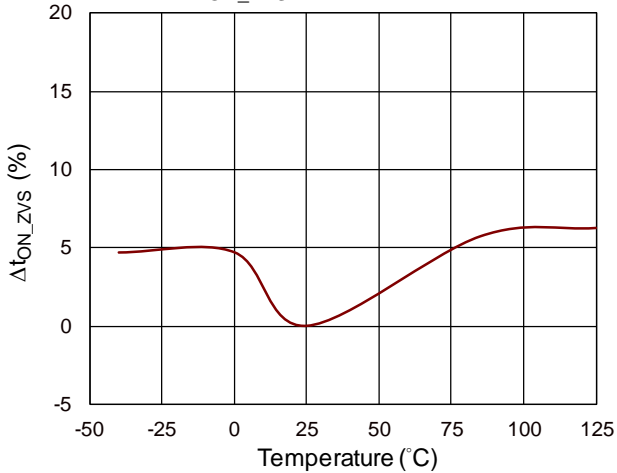
ΔV_{FR_EX} vs. Temperature



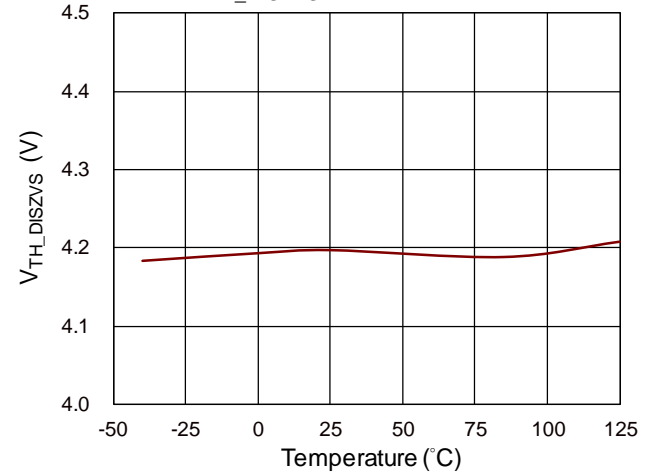
t_{D_PEAK} vs. Temperature

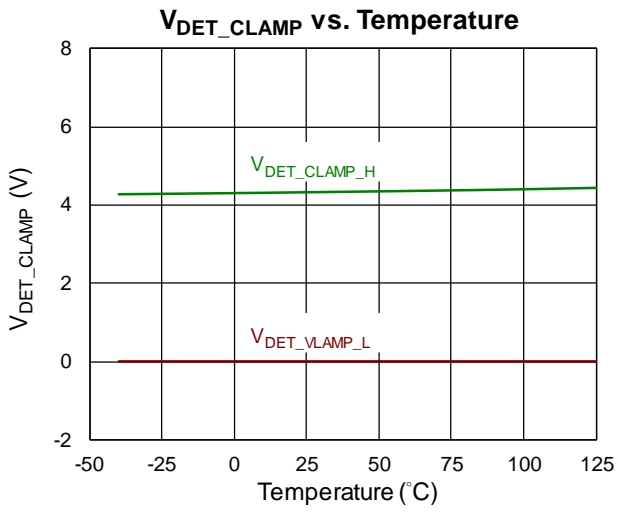


Δt_{ON_ZVS} vs. Temperature



V_{TH_DISZVS} vs. Temperature





16 Operation

The RT7220D is a secondary-side synchronous rectification controller for flyback converters operating in CCM, DCM, and QR modes. The RT7220D senses the MOSFET drain voltage to determine VG turn-on/off and modulates VG pulse width cycle-by-cycle to minimize turn-off dead time and thereby optimizing the efficiency.

16.1 Power Structure

The VDD pin supplies power to the IC and needs to be connected directly to the power supply output capacitor. The VDD pin supports a wide operating range, and the VBIAS is regulated from the LDO to supply the gate driver when output voltage is below 4.7V.

16.2 Drain Voltage Sense

The VD pin, connected to the MOSFET drain pin, is used to detect the VD signal as the VG turn-on/off criterion. The DC voltage is supplied from VD to VBIAS via a built-in HV LDO.

16.3 Gate Driver

The VG pin is a synchronous rectifier MOSFET driver, powered by either VDD or VBIAS to ensure the MOSFET can be fully turned on. In addition, the fast gate turn-off function provides reliable operation.

16.4 Source Voltage Sense

The source pin of MOSFET is connected to the input of the source voltage sensing (VS) pin. To make sure accurate sensing of the drain-sense voltage, it is strongly recommended that the sense node be directly connected to the source of the MOSFET.

16.5 ZVS Function

When the power converter operates at high input voltage, the RT7220D enables ZVS function to optimize the efficiency. The adaptive ZVS pulse on-time is modulated by V_D , V_{OUT} and R_{ZVS} .

To enable the ZVS function, the RT7220D needs to work with the RT7757D. Therefore, the last two characters in the part numbers of both the RT7220D and the RT7757D must be the same. Otherwise, the ZVS function will not operate normally. (For example, RT7757D-AE"MA" ↔ RT7220DN-L"MA")

17 Application Information

(Note 8)

17.1 Power Selection

The RT7220D supports a wide output voltage range with the VDD pin directly connected to the power output of a converter. In addition, a built-in HV LDO is used to supply the gate drive VG for the MOSFET. When VDD is less than 4.7V, the VG voltage powered by VBIAS will be clamped at 4.7V and the ZVS function is disabled. When VDD is greater than 4.7V, the VG voltage will be proportional to VDD. Once VDD is greater than 6V, the VG voltage will be clamped at 6V to ensure fast turn-off time. The power selection circuit is shown in [Figure 1](#).

Moreover, the RT7220D provides an initial pull-low function to avoid the gate of the SR MOSFET being falsely turned on by parasitic capacitance during start-up.

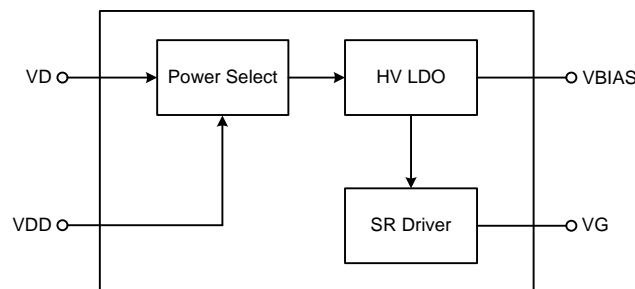


Figure 1. Power Selection Circuit

VG Turn-On

As shown in [Figure 2](#), when the VD voltage is greater than V_{VD_UVP} and the VD falling time (from $0.7 \times V_{VD_SH}$ to $V_{LOW_FALLING}$) is less than $t_{VD_FALLING}$ (150ns typ.), VG will be turned on immediately as soon as VD falls below $V_{LOW_FALLING}$.

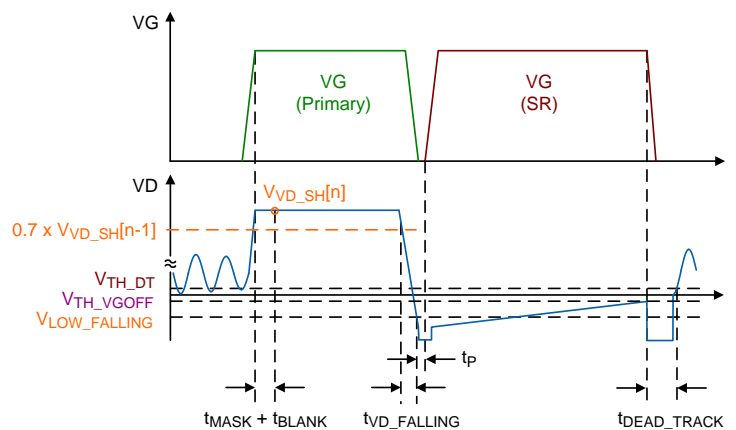


Figure 2. SR Turn-On/Off

17.2 VG Turn-Off

As shown in [Figure 2](#), VG will be turned off as the VD voltage rises to V_{TH_VGOFF} . The RT7220D modulates and optimizes the turn-off dead-time t_{DEAD_TRACK} cycle-by-cycle to provide the reliable and high efficiency operation. For the corrected dead-time modulation, the turn-off delay time of MOSFET (t_{OFF_DELAY}), as shown in [Figure 3](#), should be less than $50\% \times t_{DEAD_TRACK}$.

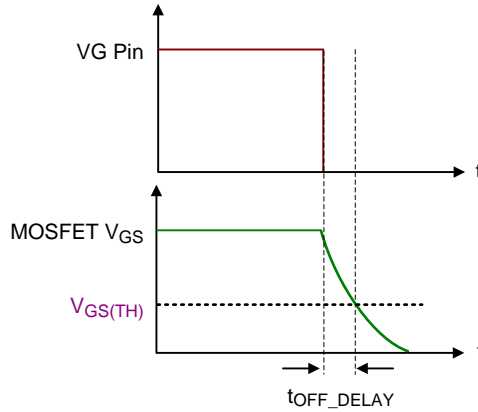


Figure 3. VG Turn-Off Delay Time

17.3 VG Minimum On-Time

The RT7220D provides a minimum on-time function to prevent incorrect turn-off due to ringing or voltage spikes. The VG turn-off threshold is blanked during tMINON_VG, as shown in [Figure 4](#).

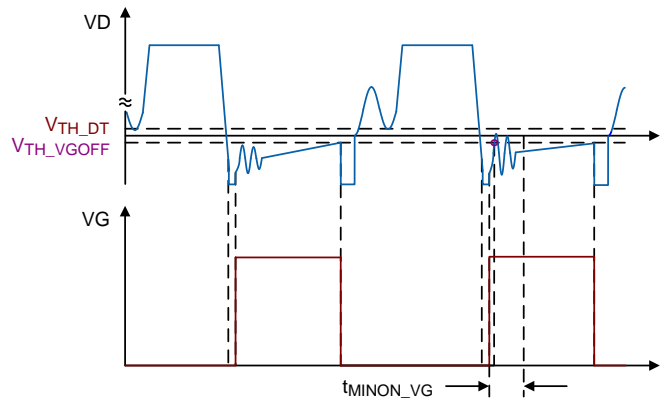


Figure 4. VG Minimum On-Time

17.4 VG Minimum Off-Time

The minimum off-time is counted from the falling edge of VG to the next rising edge of VG. During this period, the SR gate cannot be turned on to avoid false triggering of VG by the DCM ringing. The minimum off-time is shown in [Figure 5](#).

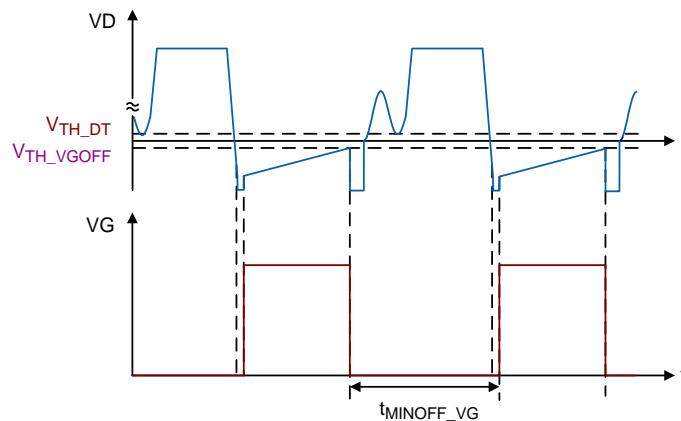


Figure 5. VG Minimum Off-Time

17.5 Green Mode Operation

To improve efficiency under light load conditions, the RT7220D features the green mode operation that disables the SR MOSFET and reduces the device operating current. The green mode is determined by detecting the number of VD and VG pulses, respectively. If VG pulses are less than 16 cycles in the period of t_{VD_EDGE} , the RT7220D disables the VG output and enters green mode, as shown in [Figure 6](#).

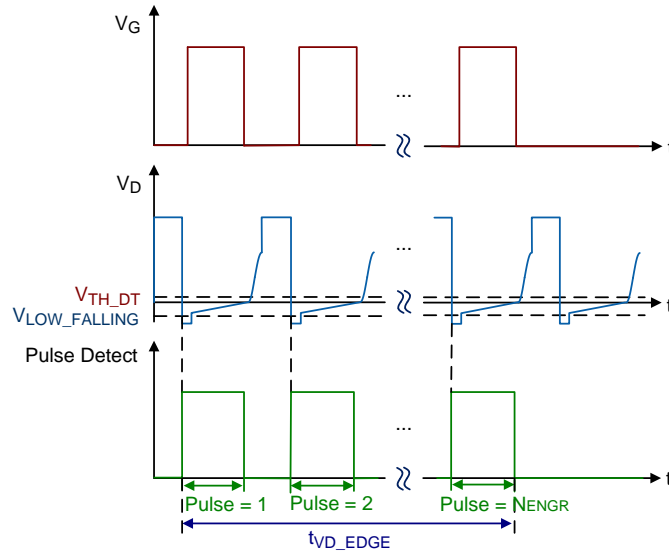


Figure 6. Entry Green Mode

Once VD pulses are greater than 32 cycles in the period of t_{VD_EDGE} , the RT7220D exits from green mode and resumes normal operation immediately, as shown in [Figure 7](#).

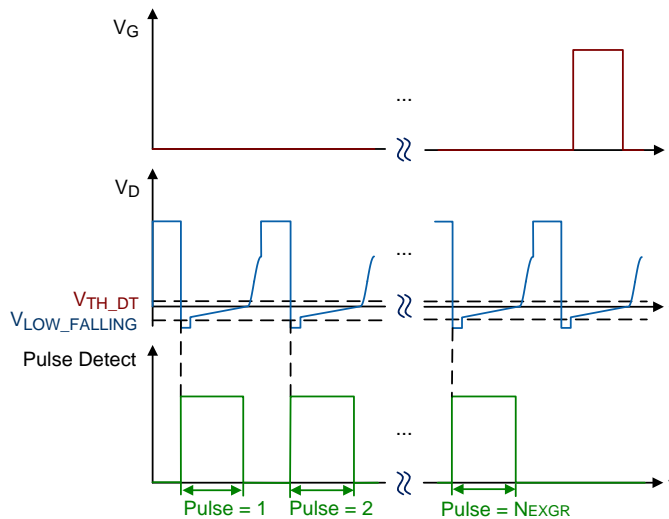


Figure 7. Exit Green Mode

17.6 Output Voltage Sense for High-Side Application

For high-side applications, since the RT7220D GND and the power converter’s GND are not the same, the VDD pin cannot sense the output voltage. Therefore, the DET pin is used to detect the output voltage.

During the SR MOSFET on-time, the DET pin outputs a clamping current that is proportional to VOUT.

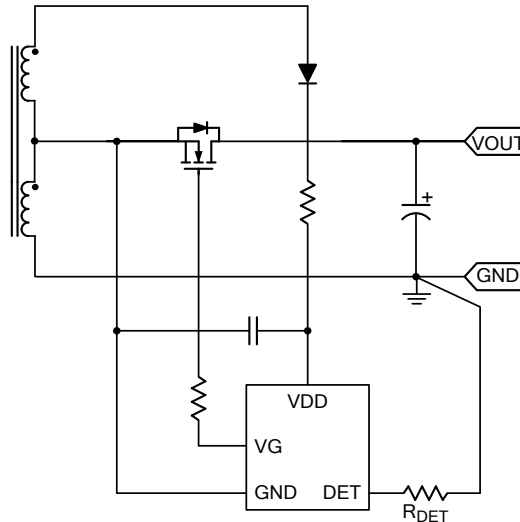


Figure 8. VOUT Sense for High-Side Applications

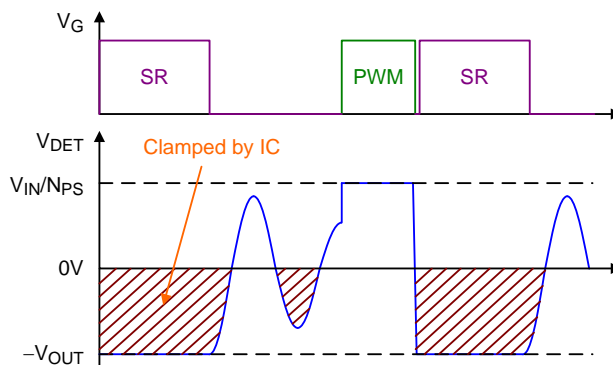


Figure 9. DET Pin Waveform

The resistance of RDET is 300kΩ and a 1% tolerance resistor is recommended. In the low-side applications, the DET pin function is disabled and should be connected to the RT7220D GND.

17.7 VD Undervoltage Protection

To avoid the RT7220D from mis-triggering VG during the AC OFF period, the SR function will be disabled when VD is lower than VVD_UVP. Since VD is equal to (VOUT + VIN/NPS), the boundary VIN of VD undervoltage protection (VIN_BOUNDARY) can be obtained according to the following equation:

$$VIN_BOUNDARY = NPS \times (VVD_UVP - VOUT)$$

where NPS is the primary-to-secondary turn ratio.

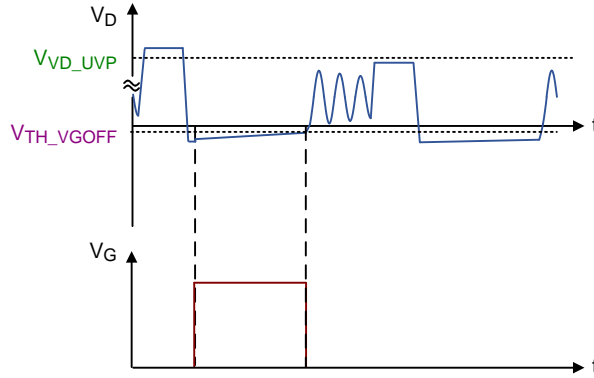


Figure 10. VD Undervoltage Protection

17.8 Frequency Control Method

When the power converter operates at high input voltage, higher output voltage and heavy load, the system will operate in ZVS mode, and the switching frequency is determined by the RT7220D. Before the primary-side MOSFET is turned on, the secondary-side MOSFET will be turned on shortly to generate a circulating current for achieving ZVS in primary-side MOSFET.

The RT7220D determines the switching frequency using a control voltage that includes the magnetic inductor L_m , the primary-to-secondary turn ratio N_{PS} , the V_{OUT} scaling ratio K_{VO} , the inductor peak current I_{peak} and the internal setting resistor R_{SET} . V_{CTL} can be expressed by the following equation:

$$V_{CTL} = (10^{11} \times K_{VO} \times L_m \times I_{peak}) / (3 \times N_{PS} \times R_{SET})$$

The internal R_{SET} can be calculated by the following equations:

$$\begin{cases} \frac{1}{2} \times L_m \times (I_{peak})^2 \times f_{SW} \times Eff. = P_O \\ f_{SW} = f_{OSC_MIN} + 271.4 \text{ (kHz/V)} \times (V_{CTL} - V_{FR_EX}) \\ V_{CTL} = \frac{10^{11} \times K_{VO} \times L_m \times I_{peak}}{3 \times N_{PS} \times R_{SET}} \end{cases}$$

17.9 ZVS Operation

When the converter operates in ZVS mode, the RT7220D detects the VD ringing to perform the ZVS operation. Once the VD ringing decreases to V_{OUT} for the debounce time t_{D_PEAK} , the ZVS pulse is turned on. The adaptive ZVS pulse on-time is modulated by VD, V_{OUT} and R_{ZVS} .

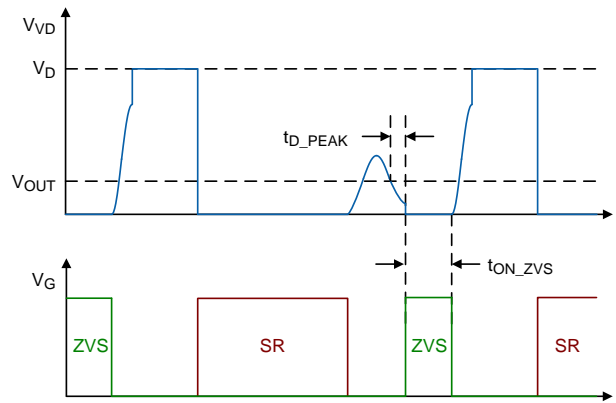


Figure 11. ZVS Operation

The external R_{ZVS} ranges from 200k Ω to 500k Ω , and a 1% tolerance resistor is recommended. The on-time of the ZVS pulse is limited from 450ns to 4.4 μ s, and it can be expressed by the following equation:

$$t_{ON_ZVS} = (V_D \times R_{ZVS}) / (1875 \times V_{OUT}) - 200 \text{ (ns)}$$

17.10 Design Considerations and PCB Layout Guide

- The bypass capacitor of VDD and VBIAS should be placed as close as possible to the RT7220D. It is recommended to use a low ESR MLCC capacitor of 1 μ F or more to reduce ripple.
- The resistor between the VD pin and the drain of the SR MOSFET is necessary. It is recommended to use a 47 Ω resistor with a package larger than 0603.
- To avoid IR voltage drop affecting the output voltage detection, the VDD pin must be connected to the output capacitor independently.
- To detect V_{DS} accurately, VS, GND and PGND must be connected to the source of the SR MOSFET independently. The ground of C_{VBIAS} and R_{ZVS} should be connected to the exposed GND pad of RT7220D for noise isolation and the exposed GND should be connected to the other GND pins.
- The SR MOSFET drive loop should be as short as possible to reduce EMI.
- For high-side applications, the auxiliary winding for VDD is required, and the VDD capacitor must be larger than 4.7 μ F.
- For high-side applications, to detect the output voltage accurately, the DET pin resistor must be connected to the GND of the output capacitor independently. The resistor R_{DET} between the DET pin and GND should be 300k Ω with a package of 0603 or larger.
- Keep the IC out of the power loop to prevent abnormal operation from noise coupling. For four-layer PCB layout, the power loop should not pass through the 2nd and 3rd PCB layers under the RT7220D chip.

17.11 Thermal Considerations

The junction temperature should never exceed the absolute maximum junction temperature $T_{J(MAX)}$, listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula:

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

where $T_{J(MAX)}$ is the maximum junction temperature; T_A is the ambient temperature; and θ_{JA} is the junction-to-ambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is normally 125°C. The junction-to-ambient thermal resistance, θ_{JA} , is highly package dependent. For a WQFN-16L 3x3 package, the thermal resistance, θ_{JA} , is 42.5°C/W on a standard JEDEC low effective-thermal-conductivity two-layer test board. The maximum power dissipation at $T_A = 25^\circ\text{C}$ can be calculated as below:

$$P_{D(MAX)} = (125^\circ\text{C} - 25^\circ\text{C}) / (42.5^\circ\text{C/W}) = 2.35\text{W for a WQFN-16L 3x3 package.}$$

The maximum power dissipation depends on the operating ambient temperature for the fixed $T_{J(MAX)}$ and the thermal resistance, θ_{JA} . The derating curve in [Figure 12](#) allows the designer to inspect the effect of rising ambient temperature on the maximum power dissipation.

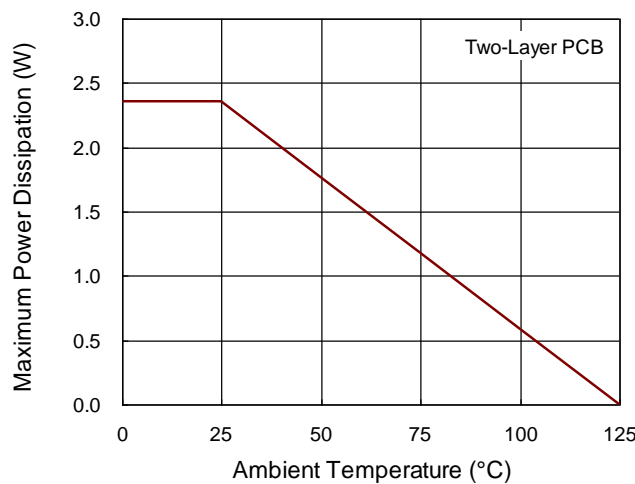
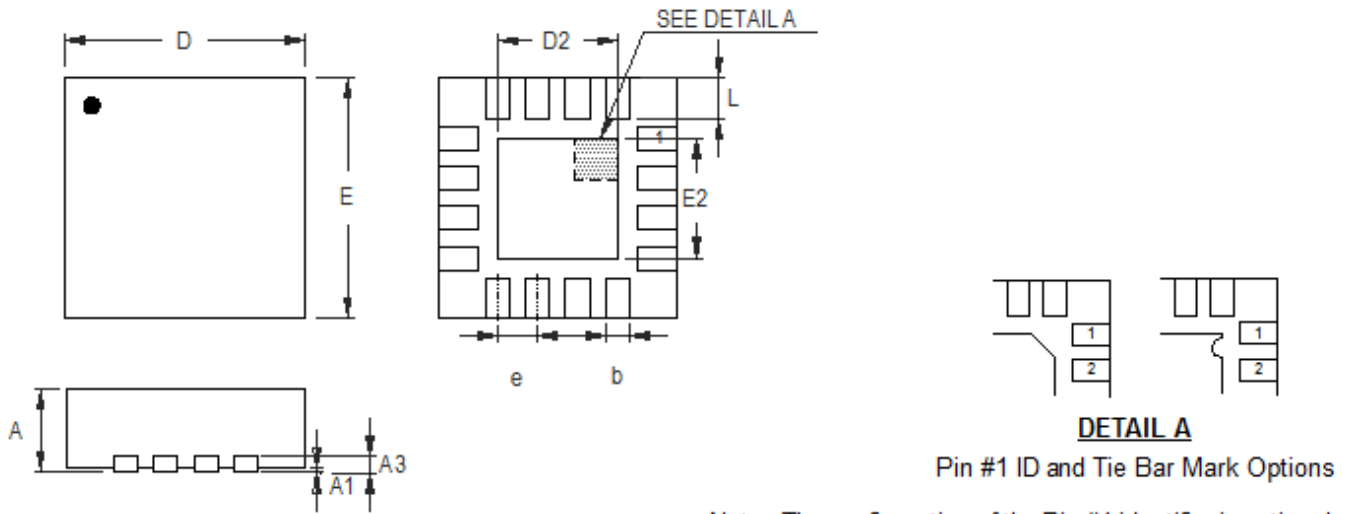


Figure 12. Derating Curve of Maximum Power Dissipation

Note 8. The information provided in this section is for reference only. The customer is solely responsible for the designing, validating, and testing your product incorporating Richtek’s product and ensure such product meets applicable standards and any safety, security, or other requirements.

18 Outline Dimension

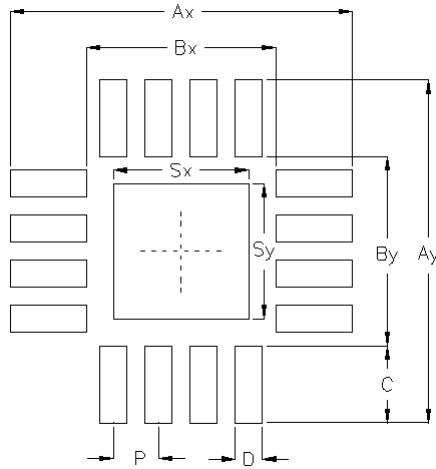


Note : The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.175	0.250	0.007	0.010
b	0.180	0.300	0.007	0.012
D	2.950	3.050	0.116	0.120
D2	1.300	1.750	0.051	0.069
E	2.950	3.050	0.116	0.120
E2	1.300	1.750	0.051	0.069
e	0.500		0.020	
L	0.350	0.450	0.014	0.018

W-Type 16L QFN 3x3 Package

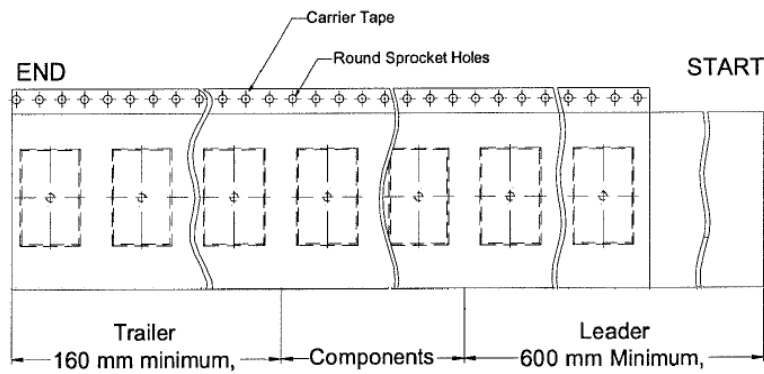
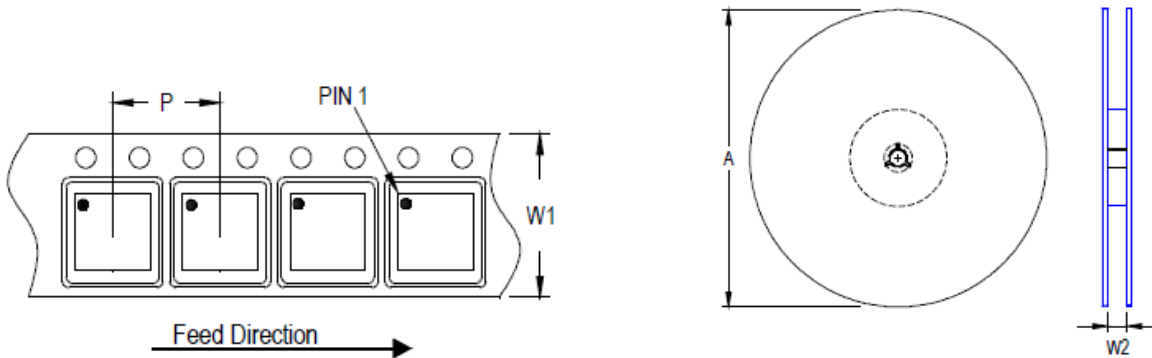
19 Footprint Information



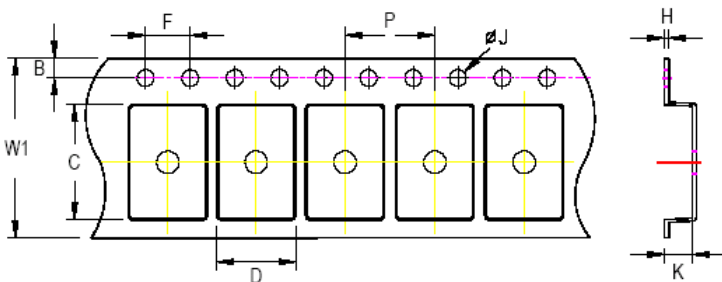
Package	Number of Pin	Footprint Dimension (mm)									Tolerance
		P	Ax	Ay	Bx	By	C	D	Sx	Sy	
V/W/U/XQFN3*3-16	16	0.50	3.80	3.80	2.10	2.10	0.85	0.30	1.50	1.50	±0.05

20 Packing Information

20.1 Tape and Reel Data









Package Type	Tape Size (W1) (mm)	Pocket Pitch (P) (mm)	Reel Size (A)		Units per Reel	Trailer (mm)	Leader (mm)	Reel Width (W2) Min./Max. (mm)
			(mm)	(in)				
QFN/DFN 3x3	8	4	180	7	3,000	160	600	8.4/9.9



C, D, and K are determined by component size.
 The clearance between the components and the cavity is as follows:
 - For 8mm carrier tape: 0.5mm max.

Tape Size	W1		P		B		F		ØJ		H
	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Max.	
12mm	12.3mm	7.9mm	8.1mm	1.65mm	1.85mm	3.9mm	4.1mm	1.5mm	1.6mm	0.6mm	

20.2 Tape and Reel Packing

Step	Photo/Description	Step	Photo/Description
1	 <p>Reel 7"</p>	4	 <p>3 reels per inner box Box A</p>
2	 <p>HIC & Desiccant (1 Unit) inside</p>	5	 <p>12 inner boxes per outer box</p>
3	 <p>Caution label is on backside of Al bag</p>	6	 <p>Outer box Carton A</p>

Package	Reel		Box			Carton		
	Size	Units	Item	Reels	Units	Item	Boxes	Unit
QFN & DFN 3x3	7"	1,500	Box A	3	9,000	Carton A	12	108,000
			Box E	1	3,000	For Combined or Partial Reel.		

20.3 Packing Material Anti-ESD Property

Surface Resistance	Aluminum Bag	Reel	Cover tape	Carrier tape	Tube	Protection Band
Ω/cm^2	10^4 to 10^{11}	10^4 to 10^{11}	10^4 to 10^{11}	10^4 to 10^{11}	10^4 to 10^{11}	10^4 to 10^{11}

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21 Datasheet Revision History

Version	Date	Description	Item
01	2023/5/22	Modify	RT7220D Version Table on P2 Absolute Maximum Ratings on P6 Recommended Operating Conditions on P6 Electrical Characteristics on P7 Application Information on P24
02	2024/7/5	Modify (Added RT7220DN-LMA)	General Description on P1 Features on P1 Ordering Information on P1 Marking Information on P2 RT7220D Version Table on P5 Note 4 on P8 Electrical Characteristics on P11, 12, 13 Typical Application Circuit on P14, 15 Typical Operating Characteristics on P20, 21, 22 Operation on P24 Application Information on P31 Packing Information on P35